Docket No.

248520US2S

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Yoshiaki FUKUZUMI

SERIAL NO: New Application

GAU:

FILED:

Herewith

EXAMINER:

FOR:

MAGNETIC MEMORY DEVICE HAVING A PLURALITY OF MAGNETO-RESISTANCE EFFECT ELEMENTS

ARRANGED IN A MATRIX FORM AND METHOD FOR MANUFACTURING THE SAME

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND, MAIER & NEUSTADT, P.C.

Marvin J. Spivak

Registration No. 24,913

C. Irvin McClelland Registration Number 21,124

Customer Number

Tel. (703) 413-3000 Fax. (703) 413-2220 (OSMMN 05/03)

LIST OF RELATED CASES

Docket Number	Serial or Patent Number	Filing or <u>Issue Date</u>	Inventor/ Applicant
242221US2RD	10/653,098	09/03/03	KAI et al.

DOCKET NO: 248520US2S Sheet <u>1</u> of <u>1</u>

IN RE APPLICATION OF: Yoshiaki FUKUZUMI

SERIAL NO: New Application

FILED: Herewith

FOR: MAGNETIC MEMORY DEVICE HAVING A PLURALITY OF MAGNETO-

RESISTANCE EFFECT ELEMENTS ARRANGED IN A MATRIX FORM AND

METHOD FOR MANUFACTURING THE SAME

STATEMENT OF RELEVANCY

Reference AA (US 6,005,800) on Form PTO- 1449:

This Patent shows similar shape of TMR.

LIST OF REFERENCES CITED BY APPLICANT Yoshiaki FUKUZUMI Flung DATE Herewith	Form PTO 1449 U.S. DEPARTMENT OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO.		SERIAL NO.							
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